

Docket No.: 67161-039

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hideto HIDAKA

Serial No.: 10/615,777

Filed: July 10, 2003

: Customer Number: 20277
: Confirmation Number: 9486
: Group Art Unit: 2811
: Examiner: To be Assigned

For: SEMICONDUCTOR MEMORY DEVICE WITH MAGNETIC DISTURBANCE REDUCED

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

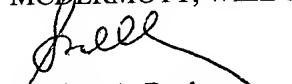
This Information Disclosure Statement and 1449 Form is supplemental to that filed July 10, 2003.

The reason for this supplemental Information Disclosure Statement and 1449 Form is to correct a typographical error made on the initial 1449 Form.. The last listed Prior Art Publication year was initially filed as 2000. The year should be changed to read 2001 as indicated on attached copies.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY


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Date: October 20, 2003



~~DEBARRED~~
INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
67161-039

SERIAL NO.
10/615,777

APPLICANT
Hideto HIDAKA

FILING DATE
July 10, 2003

GROUP
2811

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

OTHER ART (including Author, Title, etc.)		
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		SCHEUERLEIN, et al. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell" IEEE International Solid-State Circuits Conference (2000) TA 7.2
		DURLAM, et al. "Nonvolatile RAM Based on Magnetic Tunnel Junction Elements" IEEE International Solid-State Circuits Conference (2000) TA 7.3
		NAJI, et al. "A 256kb 3.0V 1T1MJT Nonvolatile Magnetoresistive RAM" IEEE International Solid-State Circuits Conference (2001) TA 7.6
EXAMINER		DATE CONSIDERED

5. ~~Consideration~~ has been considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.

*EXAMINER: Initial if reference considered, whether or not cited in this form with next communication to applicant.

Include copy of this form with next communication to applicant.
Include the unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if using a
3